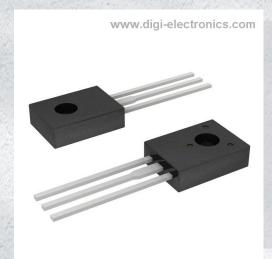


BD37716STU Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number BD37716STU-DG

Manufacturer onsemi

Manufacturer Product Number BD37716STU

Description TRANS NPN 60V 2A TO126-3

Detailed Description Bipolar (BJT) Transistor NPN 60 V 2 A 25 W Through

Hole TO-126-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BD37716STU	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	1V @ 100mA, 1A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
2μA (ICBO)	100 @ 150mA, 2V
Power - Max:	Frequency - Transition:
25 W	
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-225AA, TO-126-3	TO-126-3
Base Product Number:	
BD377	

Environmental & Export classification

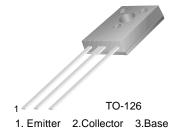
Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 29 0095



BD375/377/379

Medium Power Linear and Switching Applications

Complement to BD376, BD378 and BD380 respectively



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Parameter Value	
V _{CBO}	Collector-Base Voltage : BD375	50	V
	: BD377	75	V
	: BD379	100	V
V_{CEO}	Collector-Emitter Voltage : BD375	45	V
	: BD377	60	V
	: BD379	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	2	А
I _{CP}	*Collector Current (Pulse)	3	А
I _B	Base Current	1	А
P _C	Collector Dissipation (T _C =25°C)	25	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Paramet	er	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaini	0 0					.,
		: BD375	$I_C = 100 \text{mA}, I_B = 0$	45			V
		: BD377		60			V
		: BD379		80			V
BV _{CBO}	Collector-Base	: BD375	$I_{C} = 100 \mu A, I_{E} = 0$	50			V
	Breakdown Voltage	: BD377		75			V
		: BD379		100			V
I _{CBO}	Collector Cut-off Current	: BD375	$V_{CB} = 45V, I_{E} = 0$			2	μΑ
		: BD377	$V_{CB} = 60V, I_{E} = 0$			2	μΑ
		: BD379	$V_{CB} = 80V, I_{E} = 0$			2	μΑ
I _{EBO}	Emitter Cut-off Current		$V_{EB} = 5V, I_{C} = 0$			100	μΑ
h _{FE1}	* DC Current Gain		$V_{CE} = 2V, I_{C} = 0.15A$	40		375	
h_{FE2}			$V_{CE} = 2V, I_{C} = 1A$	20			
V _{CE} (sat)	* Collector-Emitter Saturation	on Voltage	$I_C = 1A, I_B = 0.1A$			1	V
V _{BE} (on)	* Base-Emitter ON Voltage		$V_{CE} = 2V, I_{C} = 1A$			1.5	V
t _{ON}	Turn ON Time		$V_{CC} = 30V, I_{C} = 0.5A$		50		ns
t _{OFF}	Turn OFF Time		$I_{B1} = -I_{B2} = 0.05A$ $R_{L} = 60\Omega$		500		ns

^{*} Pulse Test: PW=350µs, duty Cycle=2% Pulsed

h_{FE} Classification

Classification	6	10	16	25
h _{FE1}	40 ~ 100	63 ~ 160	100 ~ 250	150 ~ 375

Typical Characteristics

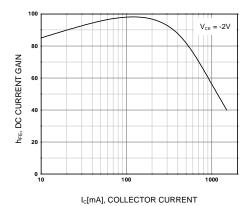


Figure 1. DC current Gain

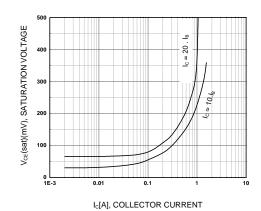


Figure 2. Collector-Emitter Saturation Voltage

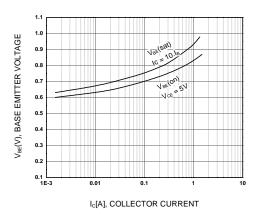


Figure 3. Base-Emitter Voltage

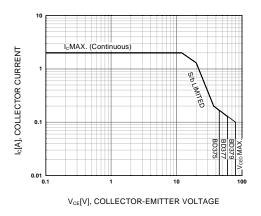


Figure 4. Safe Operating Area

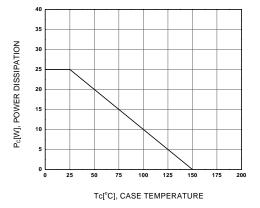
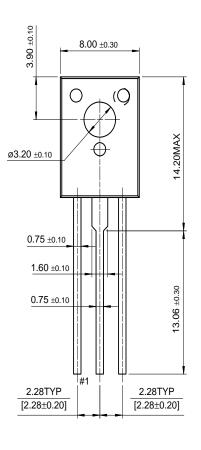
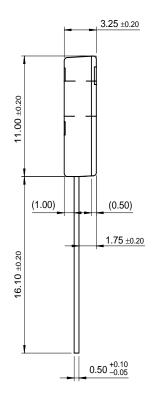


Figure 5. Power Derating

Package Demensions

TO-126





Dimensions in Millimeters

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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